# AMT1228 2 – 20GHz Low Noise Amplifier Chip

#### **Key Features :**

- Frequency range : 2 20GHz
- Typical gain : 17.5dB @ 60mA
- Input standing wave : 1.3
- Output standing wave : 1.3
- Noise figure : 2.5dB
- P-1 : 16dBm @ 10GHz
- Chip dimensions : 3.1mm x 1.3mm x 0.1mm
- Applications : wireless communication, transceiver module, radio telecommunication etc.

### **Description :**

AMT1228 chip is a Gallium Arsenide (GaAs) high performance Low Noise Amplifier, it covers 2 – 20GHz frequency range. It uses +5V single voltage operation, noise figure is 2.5dB, and 17.5dB typical gain. This chip is designed with ground through metal vias on the back technology.

#### Absolute Maximum Ratings (Ta = 25°C)

Symbol	Parameter	Value	Remark			
Vd	Drain Voltage	+7V				
Pin	Input Signal Power	17dBm				
Tch	Operating Temperature	150°C				
Tm	Sintering Temperature	310°C	30s, N <sub>2</sub> protection			
Tstg	Storage Temperature	-65 ~ +150°C				

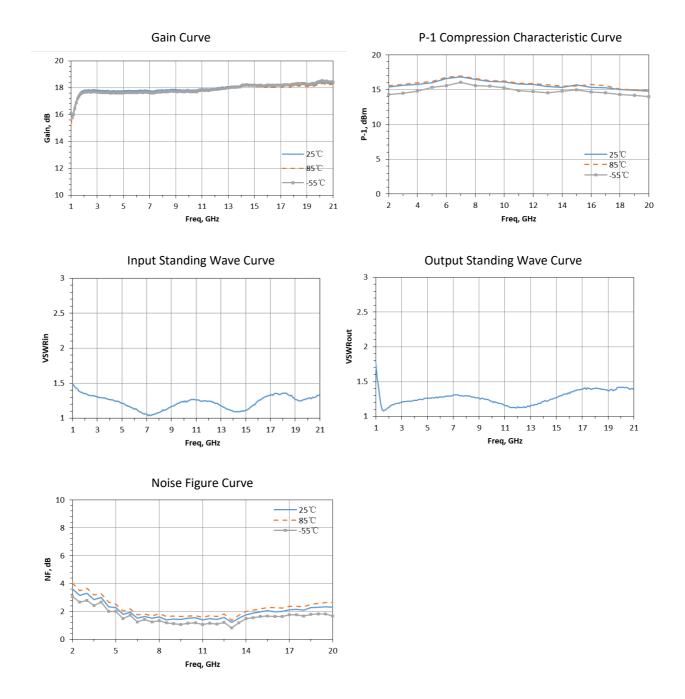
[1] Operation outside any of the Absolute Maximum Ratings may cause permanent device damage.

#### Electrical Characteristics (Ta = 25°C)

Symbol	Parameter	Test Conditions	Value			Unit
			Min	Typical	Max	
G	Gain		-	17.5	-	dB
NF	Noise Figure		-	2.5	-	dB
Id	Static Current	Vd = +5V	-	60	-	mA
VSWR_in	Input Standing Wave	F : 2 ~ 20GHz	-	1.3	-	-
VSWR_out	Output Standing Wave		-	1.3	-	-
P-1	Output Power at 1dB point		-	15.5	-	dBm



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### **Typical Performance**

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### Chip Dimensions (Unit : µm)



#### **Chip Layout Diagram**



## **Pad Definition**

Symbol	Function Description	Demensions	Equivalent Circuit
RFIN	RF signal input port, connecting to external 50 $\Omega$ system, no need to add DC blocking capacitor.	120µm*80µm	RF₋in ⊖⊣⊣⊣⊣
RFOUT	RF signal output port, connecting to external 50 $\Omega$ system, no need to add DC blocking capacitor.	120µm*80µm	−⊢⊢⊙ RF_out
VDD	Amplifier bias, need to connect 100pF external capacitor	90µm*80µm	

Please see Appendix A for details.

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